

## CLAIM AMENDMENTS

Please amend Claim 7 to read as follows:

1.-6. (Cancelled)

7. (Previously Presented) A semiconductor device comprising a single-crystal silicon active layer used for photoelectric conversion and having a (111)-plane as its surface, wherein an angle formed by any arbitrary two cutting lines, contained in the surface and not coming into coincidence, is represented by  $\theta$ , and  $\theta$  satisfies the expression  $|\cos\theta| = \frac{1}{2}$  or  $3^{1/2}/2$ .

8. (Cancelled)

9. (Previously Presented) The semiconductor device according to Claim 7, wherein any deviation of said surface from said (111) plane is within an angle equal to 24/60ths of a degree ( $0^{\circ}24'$ ).

10. (Previously Presented) A photoelectric conversion element comprising an anti-reflection layer, silicon layers, and an electrode, provided from a light incident side,

wherein all of the silicon layers are single-crystal silicon layers, and wherein the silicon layers comprise an  $n^{+}$  layer, and a  $p^{-}$  layer of about  $30\text{ }\mu\text{m}$  thickness, provided from the light incident side, wherein a surface of the silicon layers has a (111) plane, and wherein any deviation of said surface from said (111) plane is within an angle equal to 24/60ths of a degree ( $0^{\circ}24'$ ).

11. (Cancelled)

12. (Previously Presented) The photoelectric conversion element according to claim 10, wherein a  $p^{+}$  layer is provided between the  $p^{-}$  layer and the electrode, and the electrode is in contact with the  $n^{+}$  layer.